NCEP090N85QU

NCE N-Channel Super Trench II Power MOSFET

Description

The NCEP090N85QU uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

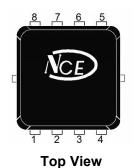
• V_{DS} =85V,I_D =56A

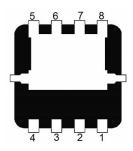
 $R_{DS(ON)}$ =8.2m Ω (typical) @ V_{GS}=10V

- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating

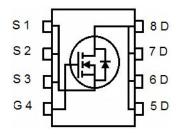
100% UIS TESTED! 100% ΔVds TESTED!

DFN 3.3X3.3









Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P090N85QU	NCEP090N85QU	DFN3.3X3.3-8L	-	-	_

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	85	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	56	А
Drain Current-Continuous(T _C =100 ℃)	I _D (100℃)	40	А
Pulsed Drain Current	I _{DM}	224	А
Maximum Power Dissipation	P _D	60	W
Derating factor		0.48	W/°C
Single pulse avalanche energy (Note 1)	E _{AS}	156	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance,Junction-to-Case	Rejc	2.08	°C/W
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NCEP090N85QU

Electrical Characteristics (T_C=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	85		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics			•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =28A	-	8.2	9.0	mΩ
Forward Transconductance	G FS	V _{DS} =5V,I _D =28A	25	-	-	S
Dynamic Characteristics						
Input Capacitance	C _{lss}	1/ 40)/1/ 0)/	-	1580	-	PF
Output Capacitance	Coss	V_{DS} =40V, V_{GS} =0V,	-	300	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz		16.5	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	t _{d(on)}		-	14	-	nS
Turn-on Rise Time	t _r	V_{DD} =40 V , I_D =28 A	-	6	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	32	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Qg	1/ 401/1 004	-	31	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =40V,I _D =28A,	-	11.6		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	8.2		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =28A	-		1.2	V
Diode Forward Current	Is		-	-	56	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 28A	-	45	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	95	-	nC

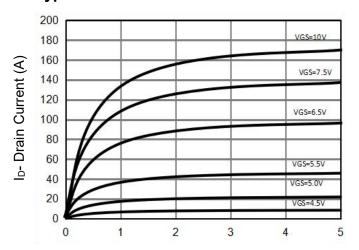
Notes:

^{1.} EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω

^{2.} Guaranteed by design, not subject to production

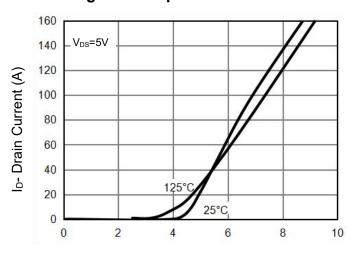
^{3.} These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=150° C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)
Figure 2 Transfer Characteristics

20
15
10
V_{GS}=10V
5
0
0 20 40 60 80 100 120 140

Rdson On-Resistance(m 12)

Figure 3 Rdson- Drain Current

I_D- Drain Current (A)

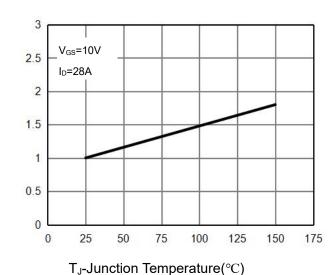


Figure 4 Rdson-Junction Temperature

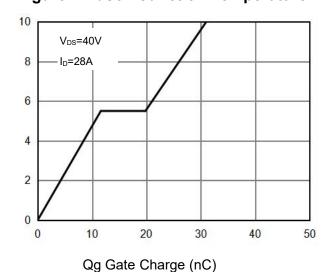
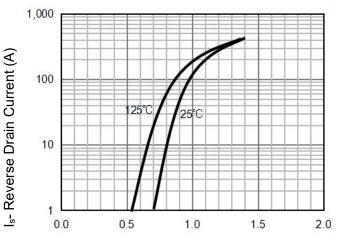


Figure 5 Gate Charge

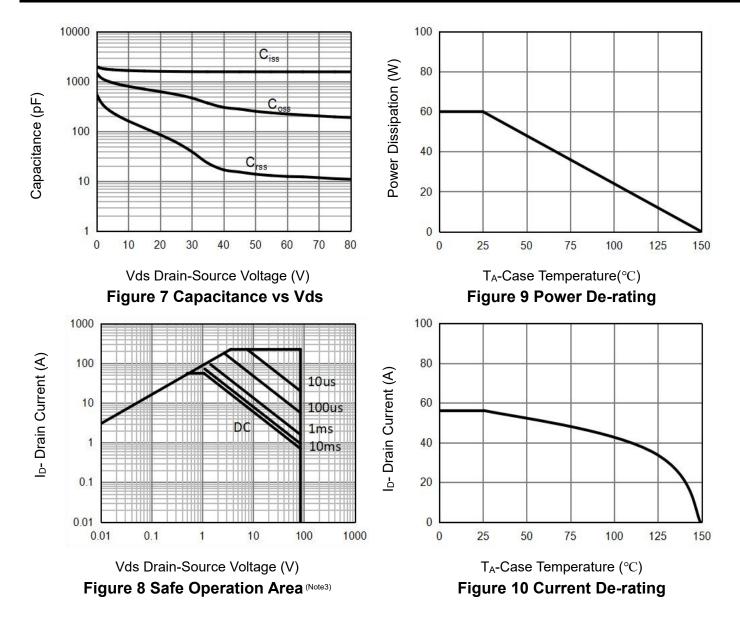


Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward

Normalized On-Resistance

Vgs Gate-Source Voltage (V)



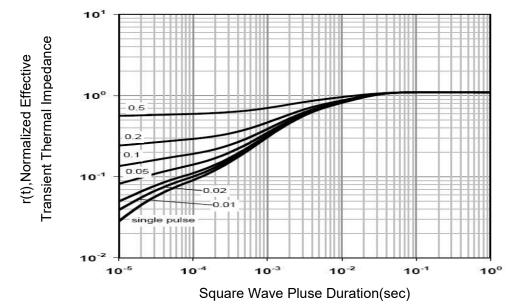
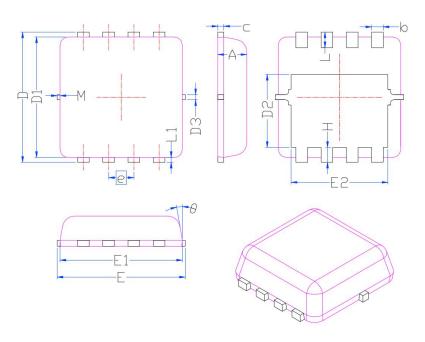


Figure 11 Normalized Maximum Transient Thermal Impedance

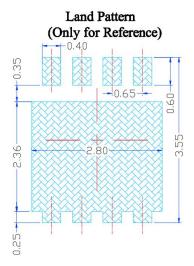
DFN3.3X3.3-8L Package Information



- Note:
 1. All Dimension Are In mm.
 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs.
 Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body
 Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash,

 Partureen The Top And Bottom Of The Plastic Body.

avi enor	DIMENSIONAL REQMTS				
SYMBOL	MIN	NOM	MAX		
A	0.70	0.75	0.80		
ь	0.25	0.30	0.35		
c	0.10	0.15	0.25		
D	3.25	3.35	3.45		
D1	3.00	3.10	3.20		
D2	1.78	1.88	1.98		
D3		0.13			
E	3.10	3.20	3.30		
E1	3.00	3.15	3.20		
E2	2.39	2.49	2.59		
e		0.65BSC			
Н	0.30	0.39	0.50		
L	0.30	0.40	0.50		
L1		0.13			
θ		10°	12°		
M	*	*	0.15		
* Not s	pecified				



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